

# Sergi Claramunt

## List of Publications by Year in descending order

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Version: 2024-02-01

22  
papers

808  
citations

933410

10  
h-index

888047

17  
g-index

22  
all docs

22  
docs citations

22  
times ranked

1499  
citing authors

#	ARTICLE	IF	CITATIONS
1	Preparation of palladium oxide nanoparticles supported on tin oxide nanofibers via modified electrospinning for ultra-low ppb NO <sub>2</sub> detection. <i>Materials Today: Proceedings</i> , 2021, 36, 1-9.	1.8	4
2	Influence of Colloidal Au on the Growth of ZnO Nanostructures. <i>Nanomaterials</i> , 2021, 11, 870.	4.1	9
3	Exploiting the KPFM capabilities to analyze at the nanoscale the impact of electrical stresses on OTFTs properties. <i>Solid-State Electronics</i> , 2021, 186, 108061.	1.4	3
4	A CAFM and device level study of MIS structures with graphene as interfacial layer for ReRAM applications. <i>Solid-State Electronics</i> , 2021, 186, 108080.	1.4	0
5	MIS structures with interfacial graphene for ReRAM applications: a nanoscale and device level characterization. , 2020, , .		1
6	Combined nanoscale KPFM characterization and device simulation for the evaluation of the MOSFET variability related to metal gate workfunction fluctuations. <i>Microelectronic Engineering</i> , 2019, 216, 111048.	2.4	0
7	Low-Power, High-Performance, Non-volatile Inkjet-Printed HfO <sub>2</sub> -Based Resistive Random Access Memory: From Device to Nanoscale Characterization. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 23659-23666.	8.0	14
8	Workfunction fluctuations in polycrystalline TiN observed with KPFM and their impact on MOSFETs variability. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	10
9	Inkjet Printed HfO <sub>2</sub> -Based ReRAMs: First Demonstration and Performance Characterization. <i>IEEE Electron Device Letters</i> , 2017, 38, 457-460.	3.9	23
10	(Invited) Advanced Measurement Techniques for the Characterization of ReRAM Devices. <i>ECS Transactions</i> , 2017, 79, 139-148.	0.5	1
11	Evaluation of ultra-thin structures composed of graphene and high-k dielectrics for resistive switching memory applications. <i>International Journal of Nanotechnology</i> , 2016, 13, 634.	0.2	0
12	CAFM Experimental Considerations and Measurement Methodology for In-Line Monitoring and Quantitative Analysis of III-V Materials Defects. <i>IEEE Nanotechnology Magazine</i> , 2016, 15, 986-992.	2.0	5
13	Conductance of Threading Dislocations in InGaAs/Si Stacks by Temperature-CAFM Measurements. <i>IEEE Electron Device Letters</i> , 2016, 37, 640-643.	3.9	9
14	The Importance of Interbands on the Interpretation of the Raman Spectrum of Graphene Oxide. <i>Journal of Physical Chemistry C</i> , 2015, 119, 10123-10129.	3.1	506
15	Non-homogeneous conduction of conductive filaments in Ni/HfO <sub>2</sub> /Si resistive switching structures observed with CAFM. <i>Microelectronic Engineering</i> , 2015, 147, 335-338.	2.4	22
16	Threading dislocations in III-V semiconductors: Analysis of electrical conduction. , 2015, , .		3
17	Flexible gas sensor array with an embedded heater based on metal decorated carbon nanofibres. <i>Sensors and Actuators B: Chemical</i> , 2013, 187, 401-406.	7.8	75
18	Flexible sensor based on carbon nanofibers with multifunctional sensing features. <i>Talanta</i> , 2013, 107, 239-247.	5.5	31

#	ARTICLE	IF	CITATIONS
19	The Role of Oxidative Debris on Graphene Oxide Films. ChemPhysChem, 2013, 14, 4002-4009.	2.1	36
20	Functionalization of Reduced Graphite Oxide Sheets with a Zwitterionic Surfactant. ChemPhysChem, 2012, 13, 3682-3690.	2.1	33
21	Advanced Performances In Gas Sensors: Stretchable, Flexible, Wireless, Wearable. Procedia Engineering, 2011, 25, 1425-1428.	1.2	6
22	Recombination dynamics in ZnO nanowires: Surfaces states versus mode quality factor. Applied Physics Letters, 2010, 97, .	3.3	17